



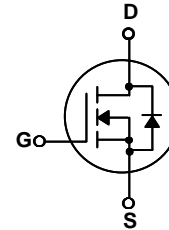
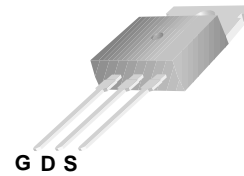
Technologies Int'l

WFP4N60

600V N-Channel MOSFET

Features

- Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Extended Safe Operating Area
- Unrivalled Gate Charge :Qg= 15nC (Typ.)
- BVDSS=600V,ID=4A
- R_{DS(on)} :2.3 Ω (Max) @VG=10V
- 100% Avalanche Tested



TO-220

G-Gate,D-Drain,S-Source

Absolute Maximum Ratings *T_c=25°C unless other wise noted*

Symbol	Parameter	WFP4N60	Units
V _{DSS}	Drain-Source Voltage	600	V
I _D	Drain Current -continuous (T _c =25°C)	4	A
	-continuous (T _c =100°C)	2.8	A
V _{GS}	Gate-Source Voltage	±30	V
E _{AS}	Single Plused Avanche Energy (Note1)	240	mJ
I _{AR}	Avalanche Current (Note2)	4	A
P _D	Power Dissipation (T _c =25°C)	100	W
T _J ,T _{STG}	Operating and Storage Temperature Range	-55 ~ +150	°C
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max	Units
R _{θJC}	Thermal Resistance,Junction to Case	--	1.18	°C/W
R _{θCS}	Thermal Resistance,Case to Sink	0.5	--	°C/W
R _{θJA}	Thermal Resistance,Junction to Ambient	--	62.5	°C/W

Electrical Characteristics Tc=25°C unless other wise noted						
Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	ID=250 μ A, VGS=0	600	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	ID=250 μ A, Reference to 25°C	--	0.6	--	V/°C
IDSS	Zero Gate Voltage Drain Current	Vds=600V, Vgs=0V	--	--	10	μ A
		Vds=480V, Tc=125°C			100	μ A
IGSSF	Gate-body leakage Current, Forward	Vgs=+30V, Vds=0V	--	--	100	nA
IGSSR	Gate-body leakage Current, Reverse	Vgs=-30V, Vds=0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	Id=250uA, Vds=Vgs	2	--	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	Id=2A, Vgs=10V	--	--	2.3	Ω
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V, VGS=0, f=1.0MHz	--	520	670	pF
Coss	Output Capacitance		--	70	90	pF
Crss	Reverse Transfer Capacitance		--	8	11	pF
Switching Characteristics						
Td(on)	Turn-On Delay Time	VDD=300V, ID=4A RG=25 Ω (Note 3,4)	--	13	35	nS
Tr	Turn-On Rise Time		--	45	100	nS
Td(off)	Turn-Off Delay Time		--	25	60	nS
Tf	Turn-Off Fall Time		--	35	80	nS
Qg	Total Gate Charge	VDS=480, VGS=10V, ID=4A (Note 3,4)	--	15	20	nC
Qgs	Gate-Source Charge		--	3.4	--	nC
Qgd	Gate-Drain Charge			7.1	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	4	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	16	A
V _{SD}	Drain-Source Diode Forward Voltage	Id=4A	--	--	1.25	V
trr	Reverse Recovery Time	I _S =4A, V _{GS} =0V	--	250	--	nS
Qrr	Reverse Recovery Charge	di _F /dt=100A/ μ s (Note3)	--	1.25	--	μ C
*Notes	1, L=27.5mH, IAS=4A, VDD=50V, RG=25Ω, Starting T _J =25°C 2, Repetitive Rating : Pulse width limited by maximum junction temperature 3, Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2% 4, Essentially Independent of Operating Temperature					

Typical Characteristics

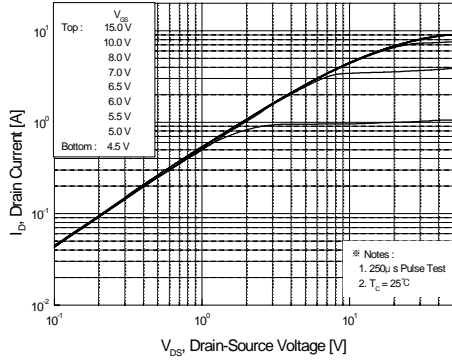


Figure 1. On-Region Characteristics

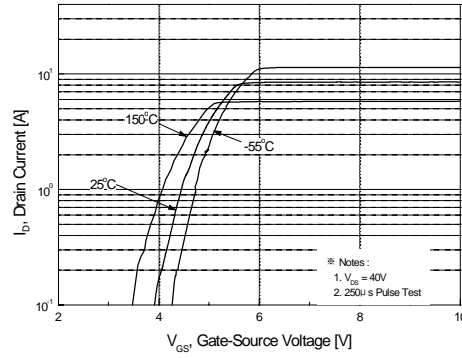


Figure 2. Transfer Characteristics

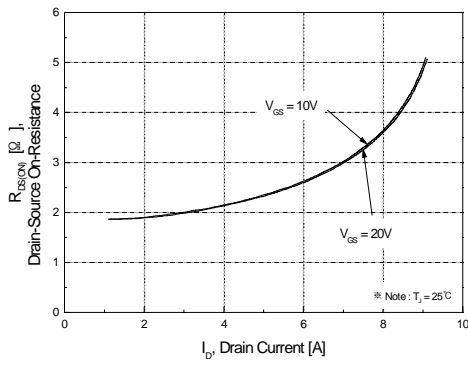


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

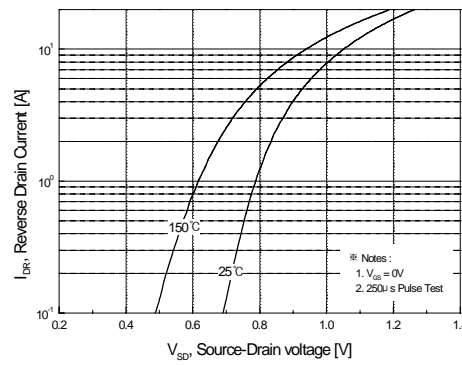


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

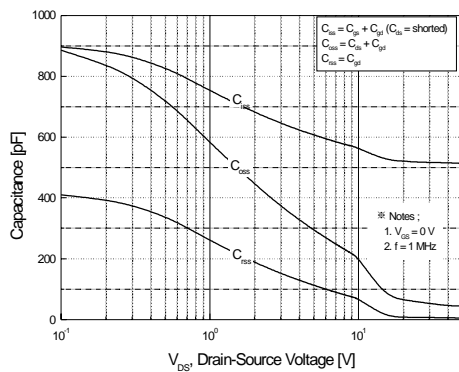


Figure 5. Capacitance Characteristics

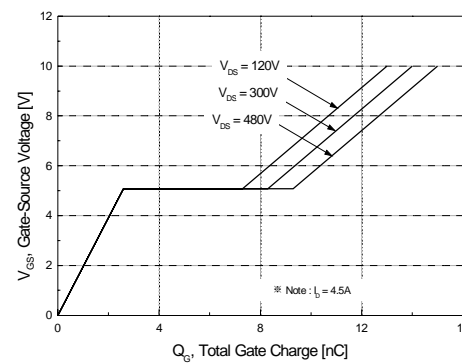


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

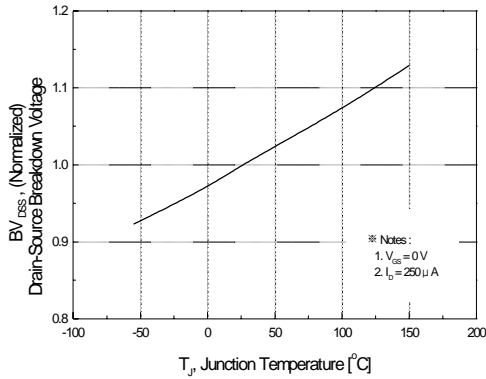


Figure 7. Breakdown Voltage Variation vs Temperature

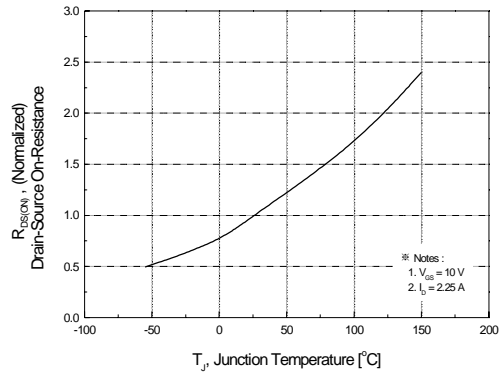


Figure 8. On-Resistance Variation vs Temperature

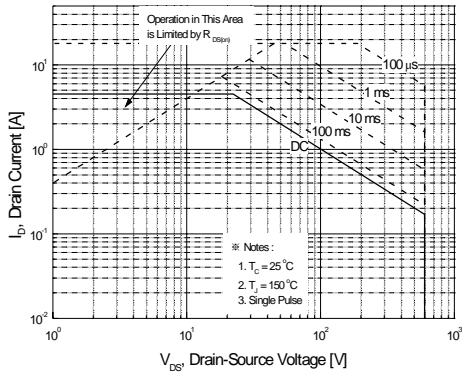


Figure 9-1. Maximum Safe Operating Area for WFP4N60

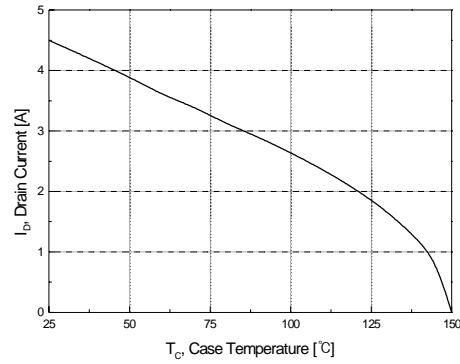


Figure 10. Maximum Drain Current vs Case Temperature

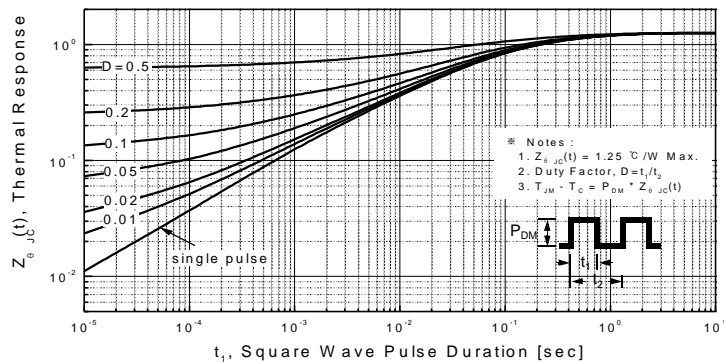
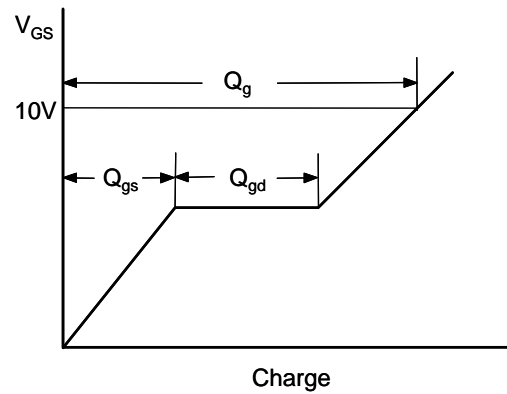
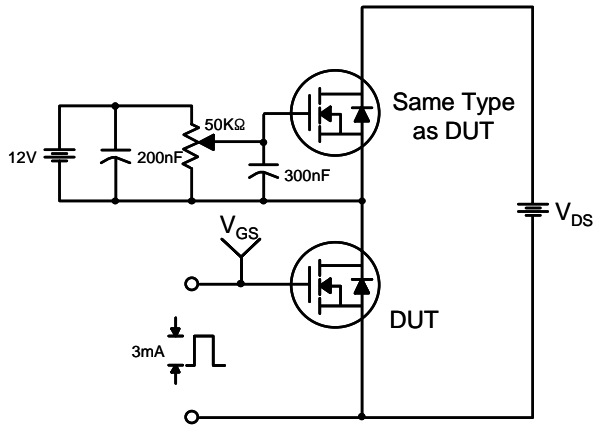
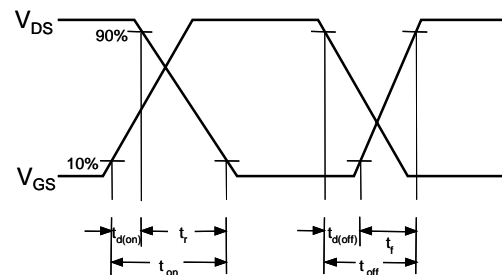
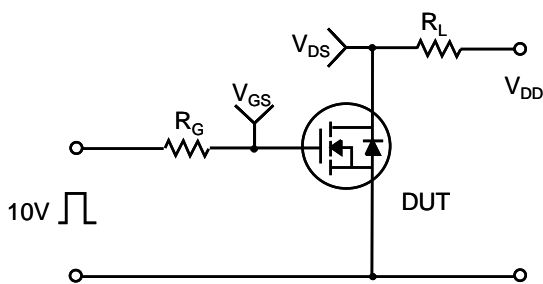


Figure 11-1. Transient Thermal Response Curve for WFP4N60

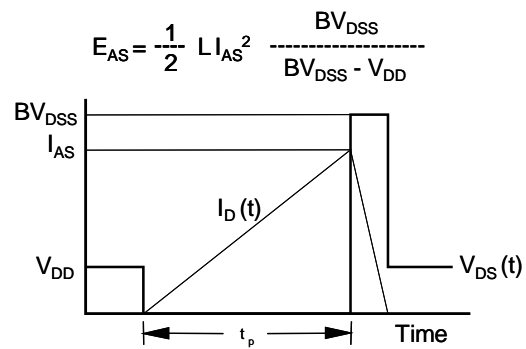
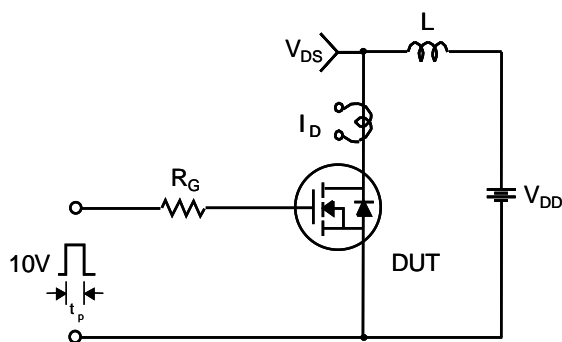
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

